

# P-Channel Enhancement-Mode Vertical DMOS FETs

#### **Features**

- ► Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- ► Low C<sub>ISS</sub> and fast switching speeds
- ▶ High input impedance and high gain
- Excellent thermal stability
- Integral source-to-drain diode

## **Applications**

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

#### **General Description**

The Supertex VP0104 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

## **Ordering Information**

Device	Package Option TO-92	BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	$R_{DS(ON)} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	l <sub>D(ON)</sub> (min) (mA)	
VP0104	VP0104N3-G	-40	8.0	-500	

<sup>-</sup>G indicates package is RoHS compliant ('Green')





## **Absolute Maximum Ratings**

Parameter	Value
Drain-to-source voltage	BV <sub>DSS</sub>
Drain-to-gate voltage	BV <sub>DGS</sub>
Gate-to-source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature*	+300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

# **Pin Configuration**



TO-92 (N3)

# **Product Marking**

SiVP 0 1 0 4 <u>YYWW</u>

YY = Year Sealed WW = Week Sealed \_\_\_\_ = "Green" Packaging

Package may or may not include the following marks: Si or

TO-92 (N3)

<sup>\*</sup> Distance of 1.6mm from case for 10 seconds.

#### **Thermal Characteristics**

Package	I <sub>D</sub> (continuous) <sup>†</sup> (mA)	I <sub>D</sub> (pulsed) (mA)	Power Dissipation @T <sub>c</sub> = 25°C (W)	θ <sub>jc</sub> (°C/W)	θ <sub>ja</sub> (°C/W)	l <sub>DR</sub> <sup>†</sup> (mA)	I <sub>DRM</sub> (mA)
TO-92	-250	-800	1.0	125	170	-250	-800

#### Notes:

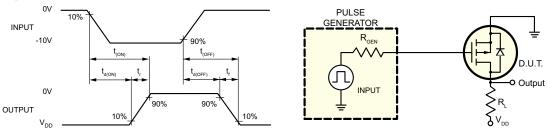
## **Electrical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

Sym	Parameter	Min	Тур	Max	Units	Conditions	
BV <sub>DSS</sub>	Drain-to-source breakdown voltage	-40	-	-	V	$V_{GS} = 0V, I_{D} = -1.0 \text{mA}$	
$V_{\rm GS(th)}$	Gate threshold voltage	-1.5	-	-3.5	V	$V_{GS} = V_{DS}$ , $I_{D} = -1.0$ mA	
$\Delta V_{GS(th)}$	Change in V <sub>GS(th)</sub> with temperature	-	5.8	6.5	mV/°C	$V_{GS} = V_{DS}$ , $I_{D} = -1.0$ mA	
I <sub>GSS</sub>	Gate body leakage current	-	-1.0	-100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
		-	-	-10	μA	$V_{GS} = 0V, V_{DS} = Max Rating$	
I <sub>DSS</sub>	Zero gate voltage drain current	-	-	-1.0	mA	$V_{DS} = 0.8$ Max Rating, $V_{GS} = 0V$ , $T_{A} = 125^{\circ}C$	
	On atata drain august	-0.15	-0.25	_		$V_{GS} = -5.0V, V_{DS} = -25V$	
D(ON)	On-state drain current	-0.5	-1.2	-	Α	$V_{GS} = -10V, V_{DS} = -25V$	
Б	Static drain-to-source	-	11	15	0	$V_{GS} = -5.0V, I_{D} = -100mA$	
R <sub>DS(ON)</sub>	on-state resistance	-	6.0	8.0	Ω	$V_{GS} = -10V, I_{D} = -500mA$	
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with temperature	-	0.55	1.0	%/°C	$V_{GS} = -10V, I_{D} = -500mA$	
G <sub>FS</sub>	Forward transconductance	150	190	-	mmho	$V_{DS} = -25V, I_{D} = -500 \text{mA}$	
C <sub>ISS</sub>	Input capacitance	-	45	60		$V_{GS} = 0V$ ,	
C <sub>oss</sub>	Common source output capacitance	-	22	30	pF	$V_{DS} = -25V$ ,	
C <sub>RSS</sub>	Reverse transfer capacitance	-	3.0	8.0		f = 1.0MHz	
t <sub>d(ON)</sub>	Turn-on delay time	-	4.0	6.0		V <sub>DD</sub> = -25V,	
t <sub>r</sub>	Rise time	-	3.0	10			
t <sub>d(OFF)</sub>	Turn-off delay time	-	8.0	12	ns	$I_D = -500 \text{mA},$ $R_{GEN} = 25\Omega$	
t <sub>f</sub>	Fall time	-	4.0	10		GEN -	
V <sub>SD</sub>	Diode forward voltage drop	-	-1.2	-2.0	V	$V_{GS} = 0V, I_{SD} = -1.0A$	
t <sub>rr</sub>	Reverse recovery time	-	400	-	ns	$V_{GS} = 0V, I_{SD} = -1.0A$	

#### Notes:

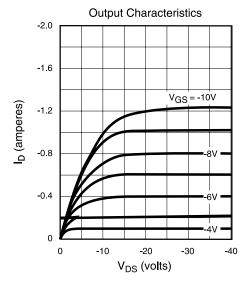
- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

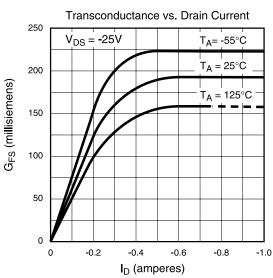
# **Switching Waveforms and Test Circuit**

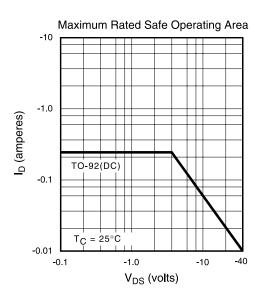


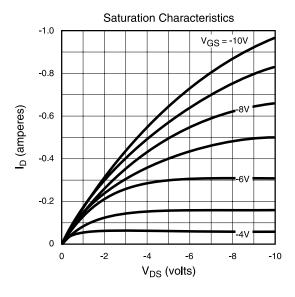
<sup>†</sup>  $I_D$  (continuous) is limited by max rated  $T_i$ .

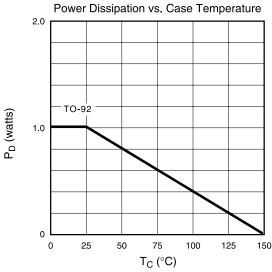
# **Typical Performance Curves**

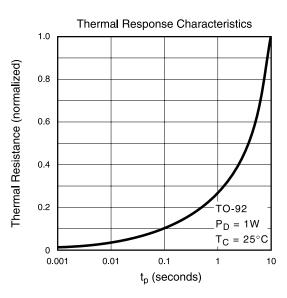




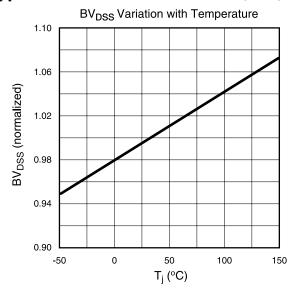


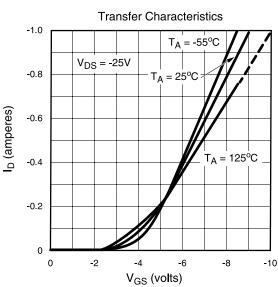


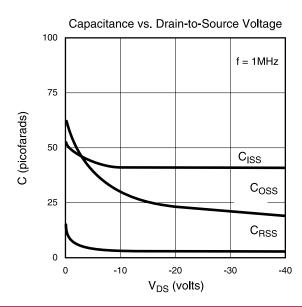


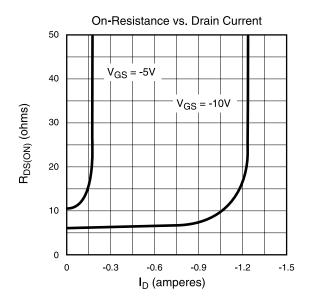


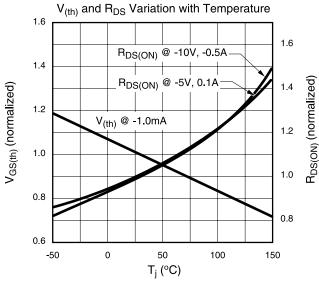
## **Typical Performance Curves** (cont.)

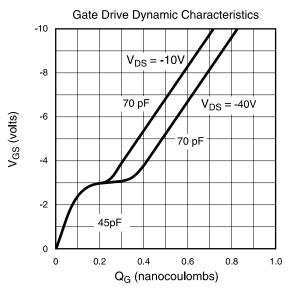




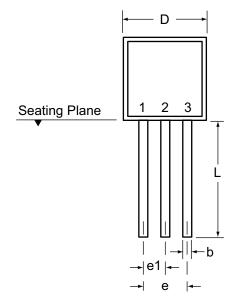


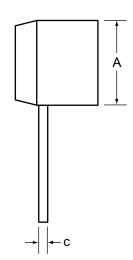






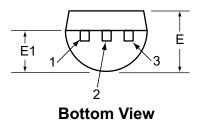
# 3-Lead TO-92 Package Outline (N3)





**Front View** 

Side View



Symbol		Α	b	С	D	E	E1	е	e1	L
Dimensions (inches)	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
	NOM	-	-	-	-	-	-	-	-	-
	MAX	.210	.022†	.022†	.205	.165	.105	.105	.055	.610*

JEDEC Registration TO-92.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing (s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="http://www.supertex.com/packaging.html">http://www.supertex.com/packaging.html</a>.)

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<sup>\*</sup> This dimension is not specified in the JEDEC drawing.

<sup>†</sup> This dimension differs from the JEDEC drawing.